

isc Silicon NPN Power Transistor

2SC3181

DESCRIPTION

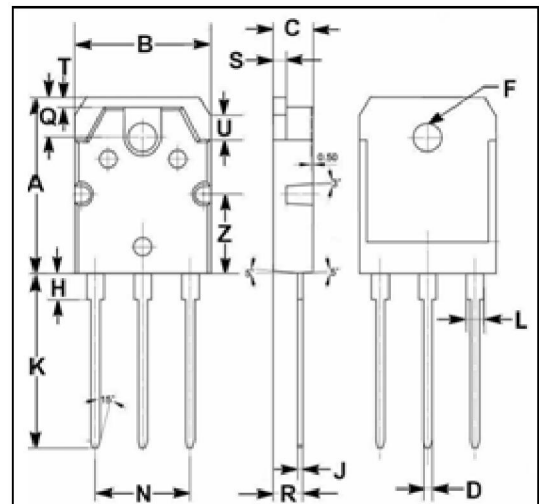
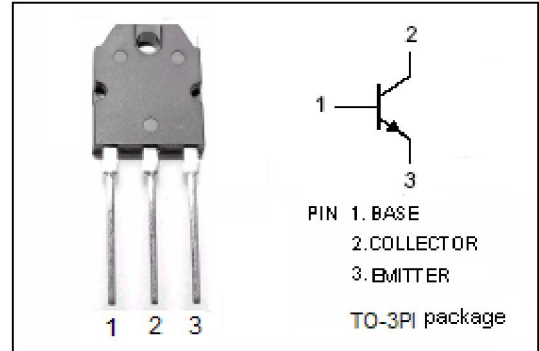
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 2.0V(\text{Max.}) @ I_C = 6A$
- Good Linearity of h_{FE}
- Complement to Type 2SA1264

APPLICATIONS

- Power amplifier applications
- Recommend for 55W high fidelity audio frequency amplifier output stage applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	8	A
I_B	Base Current-Continuous	0.8	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	80	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.40	4.60
D	0.90	1.10
F	3.20	3.40
H	2.90	3.10
J	0.50	0.70
K	19.90	20.10
L	1.90	2.10
N	10.80	11.00
Q	4.40	4.60
R	3.30	3.35
S	1.40	1.60
T	1.00	1.20
U	2.10	2.30
Z	8.90	9.10

isc Silicon NPN Power Transistor**2SC3181****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}; I_B=0$	120			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=0.6\text{A}$			2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=4\text{A}; V_{CE}=5\text{V}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=120\text{V}; I_E=0$			5	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			5	μA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	55		160	
h_{FE-2}	DC Current Gain	$I_C=4\text{A}; V_{CE}=5\text{V}$	35			
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1.0\text{MHz}$		190		pF
f_T	Current-Gain—Bandwidth Product	$I_C=1\text{A}; V_{CE}=5\text{V}$		30		MHz

◆ **h_{FE-1} Classifications**

R	O
55-110	80-160